

# MMBZxxxALT1G Series, SZMMBZxxxALT1G Series

## 24 and 40 Watt Peak Power Zener Transient Voltage Suppressors

### SOT-23 Dual Common Anode Zeners for ESD Protection

These dual monolithic silicon Zener diodes are designed for applications requiring transient overvoltage protection capability. They are intended for use in voltage and ESD sensitive equipment such as computers, printers, business machines, communication systems, medical equipment and other applications. Their dual junction common anode design protects two separate lines using only one package. These devices are ideal for situations where board space is at a premium.

#### Features

- SOT-23 Package Allows Either Two Separate Unidirectional Configurations or a Single Bidirectional Configuration
- Working Peak Reverse Voltage Range – 3 V to 26 V
- Standard Zener Breakdown Voltage Range – 5.6 V to 33 V
- Peak Power – 24 or 40 W @ 1.0 ms (Unidirectional), per Figure 6 Waveform
- ESD Rating:
  - Class 3B (> 16 kV) per the Human Body Model
  - Class C (> 400 V) per the Machine Model
- Maximum Clamping Voltage @ Peak Pulse Current
- Low Leakage < 5.0  $\mu$ A
- Flammability Rating UL 94 V-0
- AEC-Q101 Qualified and PPAP Capable
- SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements
- Pb-Free Packages are Available\*

#### Mechanical Characteristics

**CASE:** Void-free, transfer-molded, thermosetting plastic case

**FINISH:** Corrosion resistant finish, easily solderable

**MAXIMUM CASE TEMPERATURE FOR SOLDERING PURPOSES:**

260°C for 10 Seconds

Package designed for optimal automated board assembly

Small package size for high density applications

Available in 8 mm Tape and Reel

Use the Device Number to order the 7 inch/3,000 unit reel.

Replace the “T1” with “T3” in the Device Number to order the

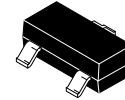
13 inch/10,000 unit reel.

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

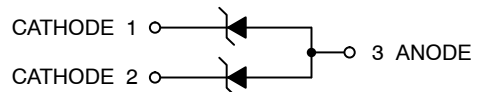


ON Semiconductor®

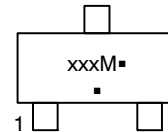
<http://onsemi.com>



SOT-23  
CASE 318  
STYLE 12



#### MARKING DIAGRAM



xxx = Specific Device Code  
M = Date Code  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

#### DEVICE MARKING INFORMATION

See specific marking information in the device marking column of the table on page 3 of this data sheet.

## MMBZxxxALT1G Series, SZMMBZxxxALT1G Series

### MAXIMUM RATINGS

| Rating   | Symbol   | Value                | Unit                       |
|--|--|----------------------|----------------------------|
| Peak Power Dissipation @ 1.0 ms (Note 1)<br>@ $T_L \leq 25^\circ\text{C}$  | MMBZ5V6ALT1G thru MMBZ9V1ALT1G<br>MMBZ12VALT1G thru MMBZ33VALT1G | $P_{pk}$<br>24<br>40 | W                          |
| Total Power Dissipation on FR-5 Board (Note 2)<br>@ $T_A = 25^\circ\text{C}$<br>Derate above $25^\circ\text{C}$        | $P_D$  | 225<br>1.8           | mW<br>mW/ $^\circ\text{C}$ |
| Thermal Resistance Junction-to-Ambient   | $R_{\theta JA}$  | 556                  | $^\circ\text{C}/\text{W}$  |
| Total Power Dissipation on Alumina Substrate (Note 3)<br>@ $T_A = 25^\circ\text{C}$<br>Derate above $25^\circ\text{C}$ | $P_D$  | 300<br>2.4           | mW<br>mW/ $^\circ\text{C}$ |
| Thermal Resistance Junction-to-Ambient   | $R_{\theta JA}$  | 417                  | $^\circ\text{C}/\text{W}$  |
| Junction and Storage Temperature Range   | $T_J, T_{stg}$   | - 55 to +150         | $^\circ\text{C}$           |
| Lead Solder Temperature - Maximum (10 Second Duration)   | $T_L$  | 260                  | $^\circ\text{C}$           |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Non-repetitive current pulse per Figure 6 and derate above  $T_A = 25^\circ\text{C}$  per Figure 7.
2. FR-5 = 1.0 x 0.75 x 0.62 in.
3. Alumina = 0.4 x 0.3 x 0.024 in, 99.5% alumina.

\*Other voltages may be available upon request.

### ORDERING INFORMATION

| Device         | Package             | Shipping <sup>†</sup> |
|----------------|---------------------|-----------------------|
| MMBZ5V6ALT1G   | SOT-23<br>(Pb-Free) | 3,000 / Tape & Reel   |
| SZMMBZ5V6ALT1G | SOT-23<br>(Pb-Free) | 3,000 / Tape & Reel   |
| MMBZ5V6ALT3G   | SOT-23<br>(Pb-Free) | 10,000 / Tape & Reel  |
| MMBZ6VxALT1G   | SOT-23<br>(Pb-Free) | 3,000 / Tape & Reel   |
| SZMMBZ6VxALT1G | SOT-23<br>(Pb-Free) | 3,000 / Tape & Reel   |
| MMBZ6VxALT3G   | SOT-23<br>(Pb-Free) | 10,000 / Tape & Reel  |
| MMBZ9V1ALT1G   | SOT-23<br>(Pb-Free) | 3,000 / Tape & Reel   |
| MMBZ9V1ALT13G  | SOT-23<br>(Pb-Free) | 10,000 / Tape & Reel  |
| MMBZxxVALT1G   | SOT-23<br>(Pb-Free) | 3,000 / Tape & Reel   |
| SZMMBZxxVALT1G | SOT-23<br>(Pb-Free) | 3,000 / Tape & Reel   |
| MMBZxxVALT3G   | SOT-23<br>(Pb-Free) | 10,000 / Tape & Reel  |
| SZMMBZxxVALT3G | SOT-23<br>(Pb-Free) | 10,000 / Tape & Reel  |

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

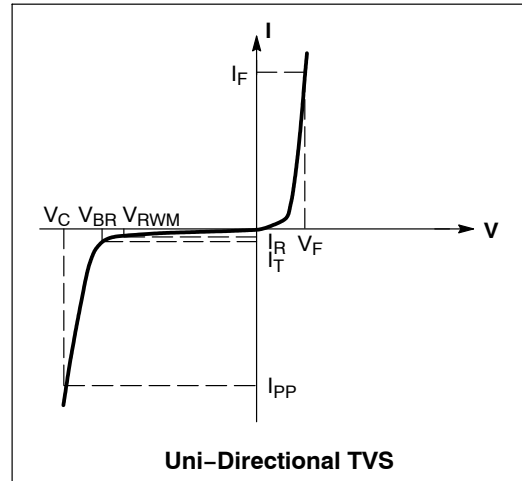
# MMBZxxxALT1G Series, SZMMBZxxxALT1G Series

## ELECTRICAL CHARACTERISTICS

(T<sub>A</sub> = 25°C unless otherwise noted)

**UNIDIRECTIONAL** (Circuit tied to Pins 1 and 3 or 2 and 3)

| Symbol           | Parameter  |
|------------------|--|
| I <sub>PP</sub>  | Maximum Reverse Peak Pulse Current                 |
| V <sub>C</sub>   | Clamping Voltage @ I <sub>PP</sub>                 |
| V <sub>RWM</sub> | Working Peak Reverse Voltage                       |
| I <sub>R</sub>   | Maximum Reverse Leakage Current @ V <sub>RWM</sub> |
| V <sub>BR</sub>  | Breakdown Voltage @ I <sub>T</sub>                 |
| I <sub>T</sub>   | Test Current                                       |
| θV <sub>BR</sub> | Maximum Temperature Coefficient of V <sub>BR</sub> |
| I <sub>F</sub>   | Forward Current                                    |
| V <sub>F</sub>   | Forward Voltage @ I <sub>F</sub>                   |
| Z <sub>ZT</sub>  | Maximum Zener Impedance @ I <sub>ZT</sub>          |
| I <sub>ZK</sub>  | Reverse Current                                    |
| Z <sub>ZK</sub>  | Maximum Zener Impedance @ I <sub>ZK</sub>          |



## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

**UNIDIRECTIONAL** (Circuit tied to Pins 1 and 3 or Pins 2 and 3)

(V<sub>F</sub> = 0.9 V Max @ I<sub>F</sub> = 10 mA)

**24 WATTS**

| Device*          | Device Marking | V <sub>RWM</sub><br>Volts | I <sub>R</sub> @<br>V <sub>RWM</sub><br>μA | Breakdown Voltage            |     |      |                  | Max Zener Impedance (Note 5)         |                                   |                | V <sub>C</sub> @ I <sub>PP</sub> (Note 6) |      | θV <sub>BR</sub><br>mV/°C |
|------------------|----------------|---------------------------|--|------------------------------|-----|------|------------------|--------------------------------------|-----------------------------------|----------------|---|------|---------------------------|
|                  |                |                           |  | V <sub>BR</sub> (Note 4) (V) |     |      | @ I <sub>T</sub> | Z <sub>ZT</sub><br>@ I <sub>ZT</sub> | Z <sub>ZK</sub> @ I <sub>ZK</sub> | V <sub>C</sub> | I <sub>PP</sub>                           |      |                           |
|                  |                |                           |  | Min                          | Nom | Max  | mA               | Ω                                    | Ω                                 | mA             | V   | A    |                           |
| MMBZ5V6ALT1G/T3G | 5A6            | 3.0                       | 5.0  | 5.32                         | 5.6 | 5.88 | 20               | 11                                   | 1600                              | 0.25           | 8.0                                       | 3.0  | 1.26                      |
| MMBZ6V2ALT1G     | 6A2            | 3.0                       | 0.5  | 5.89                         | 6.2 | 6.51 | 1.0              | -                                    | -                                 | -              | 8.7                                       | 2.76 | 2.80                      |
| MMBZ6V8ALT1G     | 6A8            | 4.5                       | 0.5  | 6.46                         | 6.8 | 7.14 | 1.0              | -                                    | -                                 | -              | 9.6                                       | 2.5  | 3.4                       |
| MMBZ9V1ALT1G     | 9A1            | 6.0                       | 0.3  | 8.65                         | 9.1 | 9.56 | 1.0              | -                                    | -                                 | -              | 14  | 1.7  | 7.5                       |

(V<sub>F</sub> = 0.9 V Max @ I<sub>F</sub> = 10 mA)

**40 WATTS**

| Device*          | Device Marking | V <sub>RWM</sub><br>Volts | I <sub>R</sub> @<br>V <sub>RWM</sub><br>nA | Breakdown Voltage            |     |       |                  | V <sub>C</sub> @ I <sub>PP</sub> (Note 6) |                 | θV <sub>BR</sub><br>mV/°C |
|------------------|----------------|---------------------------|--|------------------------------|-----|-------|------------------|---|-----------------|---------------------------|
|                  |                |                           |  | V <sub>BR</sub> (Note 4) (V) |     |       | @ I <sub>T</sub> | V <sub>C</sub>                            | I <sub>PP</sub> |                           |
|                  |                |                           |  | Min                          | Nom | Max   | mA               | V   | A               |                           |
| MMBZ12VALT1G     | 12A            | 8.5                       | 200  | 11.40                        | 12  | 12.60 | 1.0              | 17  | 2.35            | 7.5                       |
| MMBZ15VALT1G     | 15A            | 12                        | 50   | 14.25                        | 15  | 15.75 | 1.0              | 21  | 1.9             | 12.3                      |
| MMBZ18VALT1G     | 18A            | 14.5                      | 50   | 17.10                        | 18  | 18.90 | 1.0              | 25  | 1.6             | 15.3                      |
| MMBZ20VALT1G     | 20A            | 17                        | 50   | 19.00                        | 20  | 21.00 | 1.0              | 28  | 1.4             | 17.2                      |
| MMBZ27VALT1G/T3G | 27A            | 22                        | 50   | 25.65                        | 27  | 28.35 | 1.0              | 40  | 1.0             | 24.3                      |
| MMBZ33VALT1G     | 33A            | 26                        | 50   | 31.35                        | 33  | 34.65 | 1.0              | 46  | 0.87            | 30.4                      |

4. V<sub>BR</sub> measured at pulse test current I<sub>T</sub> at an ambient temperature of 25°C.

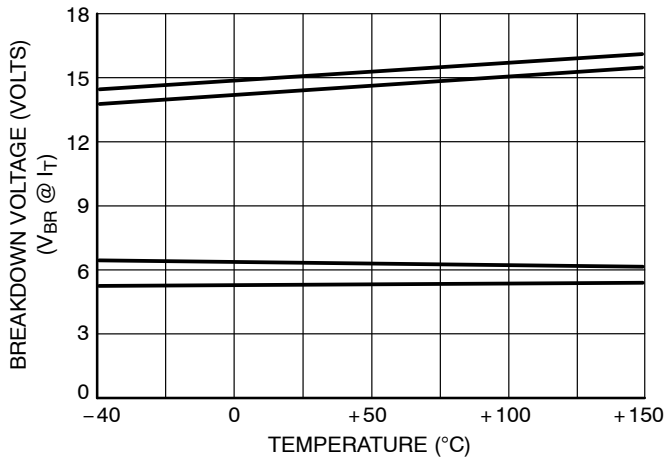
5. Z<sub>ZT</sub> and Z<sub>ZK</sub> are measured by dividing the AC voltage drop across the device by the AC current applied. The specified limits are for I<sub>Z(AC)</sub> = 0.1 I<sub>Z(DC)</sub>, with the AC frequency = 1.0 kHz.

6. Surge current waveform per Figure 6 and derate per Figure 7

\* Include SZ-prefix devices where applicable.

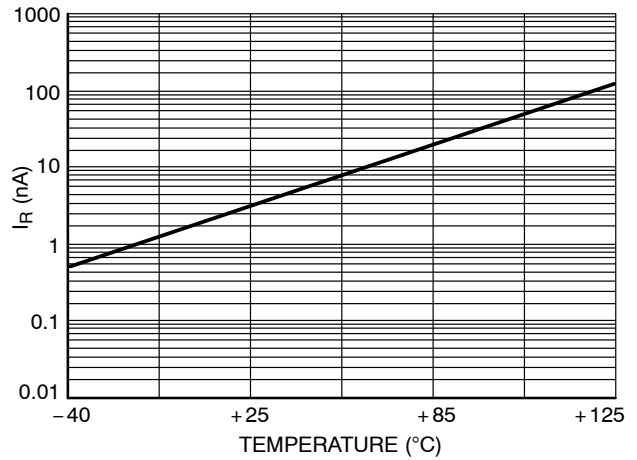
# MMBZxxxALT1G Series, SZMMBZxxxALT1G Series

## TYPICAL CHARACTERISTICS

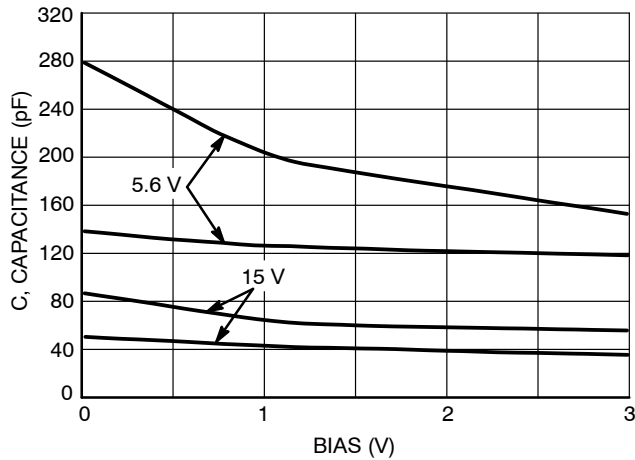


**Figure 1. Typical Breakdown Voltage versus Temperature**

(Upper curve for each voltage is bidirectional mode, lower curve is unidirectional mode)

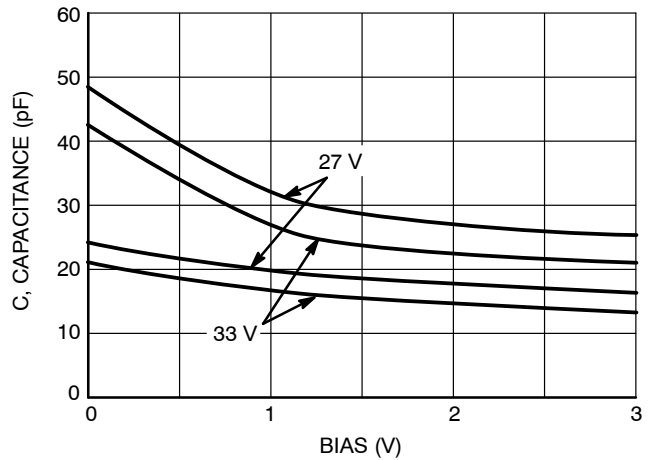


**Figure 2. Typical Leakage Current versus Temperature**



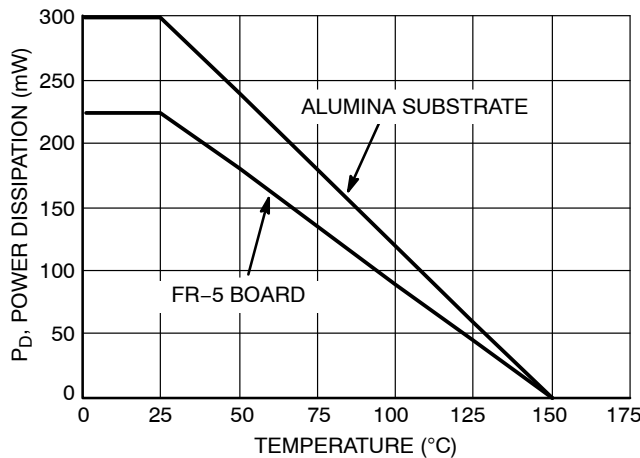
**Figure 3. Typical Capacitance versus Bias Voltage**

(Upper curve for each voltage is unidirectional mode, lower curve is bidirectional mode)



**Figure 4. Typical Capacitance versus Bias Voltage**

(Upper curve for each voltage is unidirectional mode, lower curve is bidirectional mode)



**Figure 5. Steady State Power Derating Curve**

TYPICAL CHARACTERISTICS

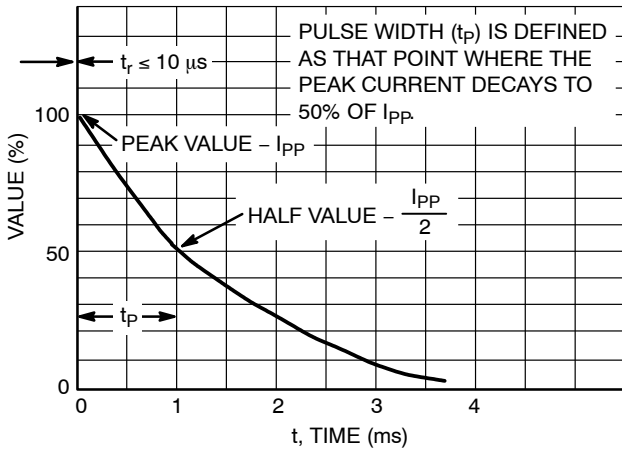


Figure 6. Pulse Waveform

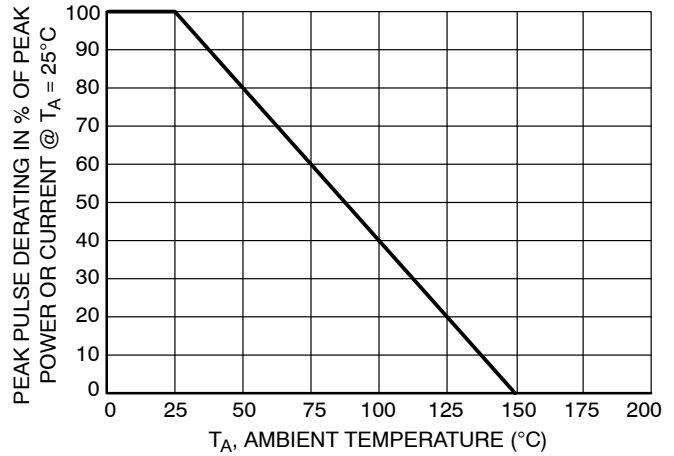


Figure 7. Pulse Derating Curve

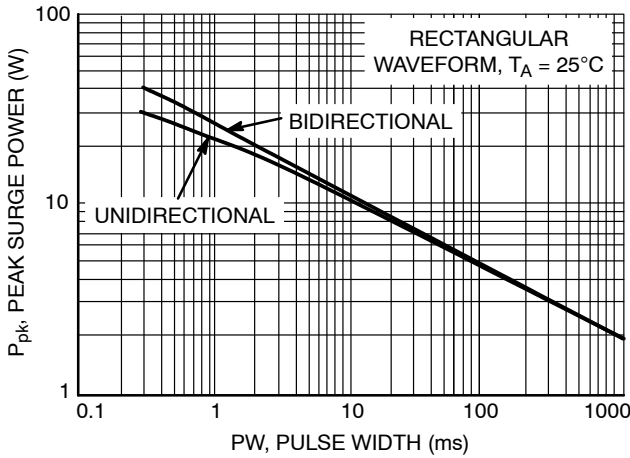


Figure 8. Maximum Non-repetitive Surge Power,  $P_{pk}$  versus PW

Power is defined as  $V_{RSM} \times I_Z(pk)$  where  $V_{RSM}$  is the clamping voltage at  $I_Z(pk)$ .

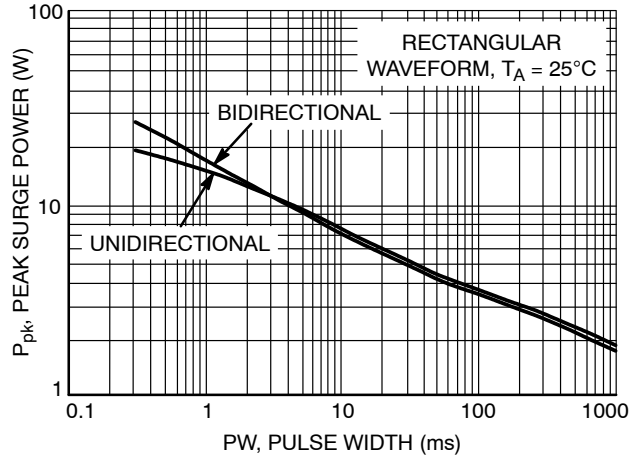


Figure 9. Maximum Non-repetitive Surge Power,  $P_{pk(NOM)}$  versus PW

Power is defined as  $V_Z(NOM) \times I_Z(pk)$  where  $V_Z(NOM)$  is the nominal Zener voltage measured at the low test current used for voltage classification.

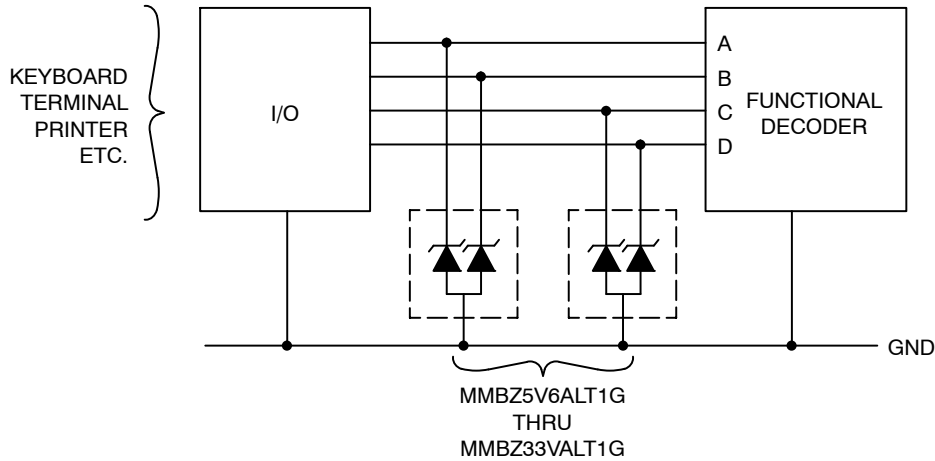
# MMBZxxxALT1G Series, SZMMBZxxxALT1G Series

## TYPICAL COMMON ANODE APPLICATIONS

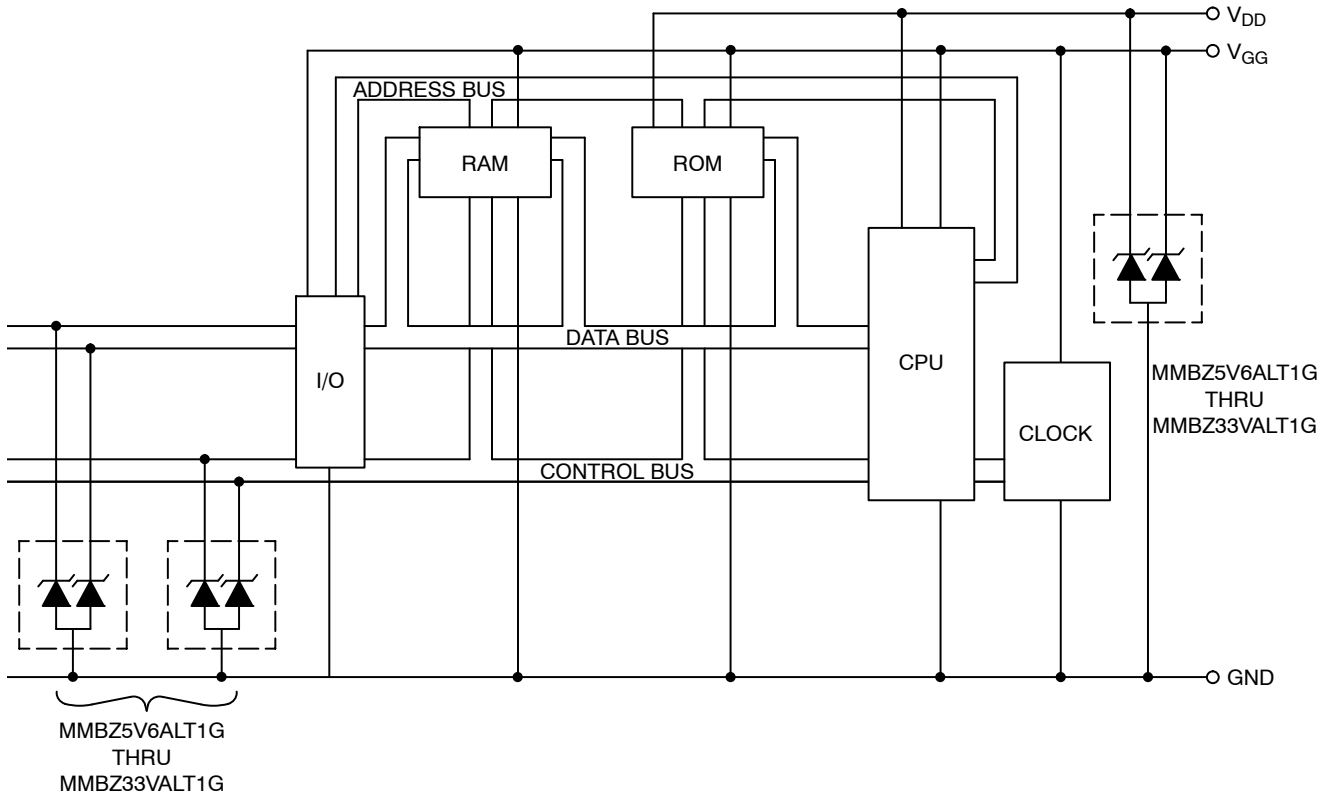
A quad junction common anode design in a SOT-23 package protects four separate lines using only one package. This adds flexibility and creativity to PCB design especially

when board space is at a premium. Two simplified examples of TVS applications are illustrated below.

### Computer Interface Protection



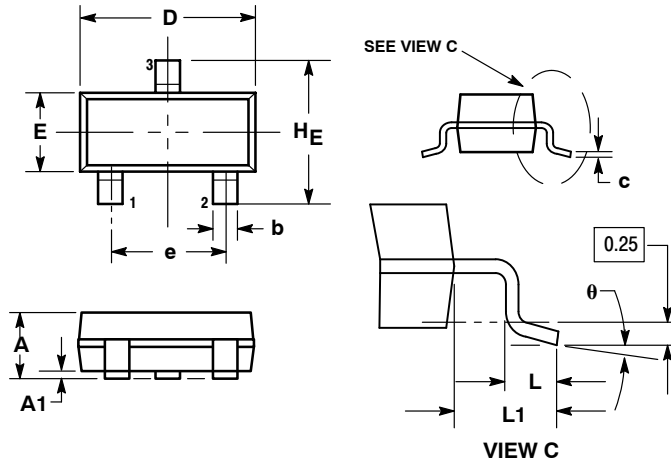
### Microprocessor Protection



# MMBZxxxALT1G Series, SZMMBZxxxALT1G Series

## PACKAGE DIMENSIONS

SOT-23 (TO-236)  
CASE 318-08  
ISSUE AP

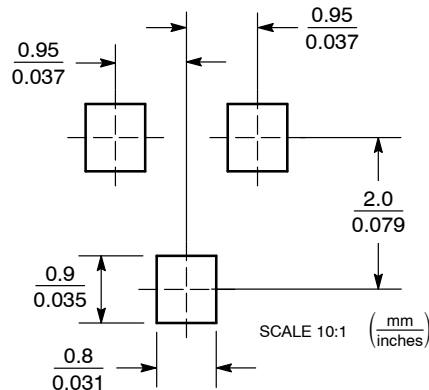


- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
  4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

| DIM | MILLIMETERS |      |      | INCHES |       |       |
|-----|-------------|------|------|--------|-------|-------|
|     | MIN         | NOM  | MAX  | MIN    | NOM   | MAX   |
| A   | 0.89        | 1.00 | 1.11 | 0.035  | 0.040 | 0.044 |
| A1  | 0.01        | 0.06 | 0.10 | 0.001  | 0.002 | 0.004 |
| b   | 0.37        | 0.44 | 0.50 | 0.015  | 0.018 | 0.020 |
| c   | 0.09        | 0.13 | 0.18 | 0.003  | 0.005 | 0.007 |
| D   | 2.80        | 2.90 | 3.04 | 0.110  | 0.114 | 0.120 |
| E   | 1.20        | 1.30 | 1.40 | 0.047  | 0.051 | 0.055 |
| e   | 1.78        | 1.90 | 2.04 | 0.070  | 0.075 | 0.081 |
| L   | 0.10        | 0.20 | 0.30 | 0.004  | 0.008 | 0.012 |
| L1  | 0.35        | 0.54 | 0.69 | 0.014  | 0.021 | 0.029 |
| HE  | 2.10        | 2.40 | 2.64 | 0.083  | 0.094 | 0.104 |
| θ   | 0°          | ---  | 10°  | 0°     | ---   | 10°   |

- STYLE 12:  
PIN 1. CATHODE  
2. CATHODE  
3. ANODE

## SOLDERING FOOTPRINT



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

## PUBLICATION ORDERING INFORMATION

**LITERATURE FULFILLMENT:**  
Literature Distribution Center for ON Semiconductor  
P.O. Box 5163, Denver, Colorado 80217 USA  
**Phone:** 303-675-2175 or 800-344-3860 Toll Free USA/Canada  
**Fax:** 303-675-2176 or 800-344-3867 Toll Free USA/Canada  
**Email:** orderlit@onsemi.com

**N. American Technical Support:** 800-282-9855 Toll Free  
USA/Canada  
**Europe, Middle East and Africa Technical Support:**  
Phone: 421 33 790 2910  
**Japan Customer Focus Center**  
Phone: 81-3-5817-1050

**ON Semiconductor Website:** [www.onsemi.com](http://www.onsemi.com)  
**Order Literature:** <http://www.onsemi.com/orderlit>  
For additional information, please contact your local Sales Representative

Компания «Океан Электроники» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Поставка оригинальных импортных электронных компонентов напрямую с производств Америки, Европы и Азии, а так же с крупнейших складов мира;
- Широкая линейка поставок активных и пассивных импортных электронных компонентов (более 30 млн. наименований);
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Помощь Конструкторского Отдела и консультации квалифицированных инженеров;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Поставка электронных компонентов под контролем ВП;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- При необходимости вся продукция военного и аэрокосмического назначения проходит испытания и сертификацию в лаборатории (по согласованию с заказчиком);
- Поставка специализированных компонентов военного и аэрокосмического уровня качества (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Actel, Aeroflex, Peregrine, VPT, Syfer, Eurofarad, Texas Instruments, MS Kennedy, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Компания «Океан Электроники» является официальным дистрибьютором и эксклюзивным представителем в России одного из крупнейших производителей разъемов военного и аэрокосмического назначения «JONHON», а так же официальным дистрибьютором и эксклюзивным представителем в России производителя высокотехнологичных и надежных решений для передачи СВЧ сигналов «FORSTAR».



## JONHON

«JONHON» (основан в 1970 г.)

Разъемы специального, военного и аэрокосмического назначения:

(Применяются в военной, авиационной, аэрокосмической, морской, железнодорожной, горно- и нефтедобывающей отраслях промышленности)

«FORSTAR» (основан в 1998 г.)

ВЧ соединители, коаксиальные кабели, кабельные сборки и микроволновые компоненты:

(Применяются в телекоммуникациях гражданского и специального назначения, в средствах связи, РЛС, а так же военной, авиационной и аэрокосмической отраслях промышленности).



Телефон: 8 (812) 309-75-97 (многоканальный)

Факс: 8 (812) 320-03-32

Электронная почта: [ocean@oceanchips.ru](mailto:ocean@oceanchips.ru)

Web: <http://oceanchips.ru/>

Адрес: 198099, г. Санкт-Петербург, ул. Калинина, д. 2, корп. 4, лит. А